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"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

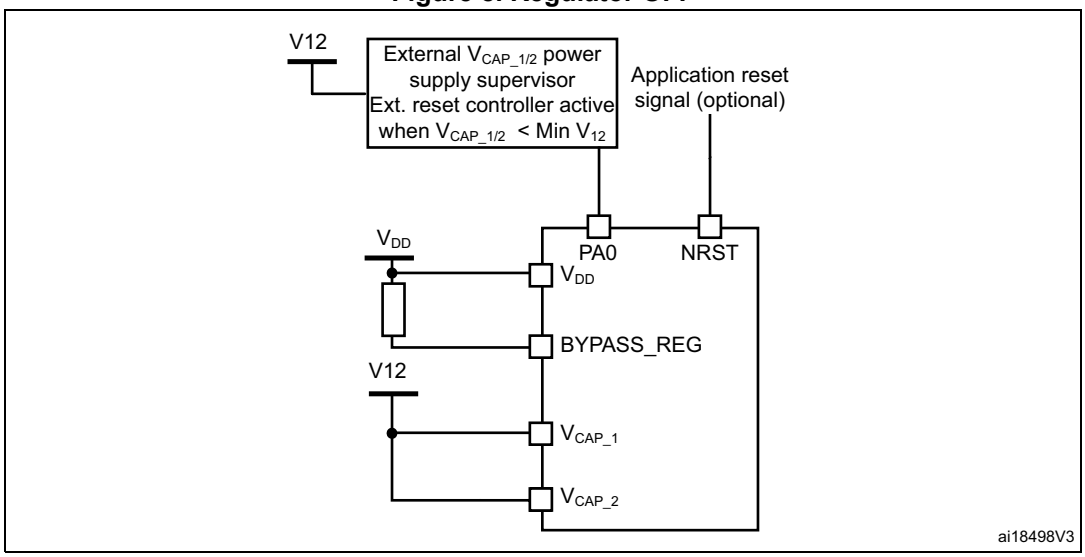
Details	
Product Status	Active
Core Processor	ARM® Cortex®-M4
Core Size	32-Bit Single-Core
Speed	180MHz
Connectivity	CANbus, EBI/EMI, Ethernet, I²C, IrDA, LINbus, SPI, UART/USART, USB OTG
Peripherals	Brown-out Detect/Reset, DMA, I²S, LCD, POR, PWM, WDT
Number of I/O	168
Program Memory Size	1MB (1M x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	256K x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 3.6V
Data Converters	A/D 24x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	208-LQFP
Supplier Device Package	208-LQFP (28x28)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32f429bgt6

List of tables

In regulator OFF mode, the following features are no more supported:

- PA0 cannot be used as a GPIO pin since it allows to reset a part of the V_{12} logic power domain which is not reset by the NRST pin.
- As long as PA0 is kept low, the debug mode cannot be used under power-on reset. As a consequence, PA0 and NRST pins must be managed separately if the debug connection under reset or pre-reset is required.
- The over-drive and under-drive modes are not available.
- The Standby mode is not available.

Figure 8. Regulator OFF



The following conditions must be respected:

- V_{DD} should always be higher than V_{CAP_1} and V_{CAP_2} to avoid current injection between power domains.
- If the time for V_{CAP_1} and V_{CAP_2} to reach V_{12} minimum value is faster than the time for V_{DD} to reach 1.7 V, then PA0 should be kept low to cover both conditions: until V_{CAP_1} and V_{CAP_2} reach V_{12} minimum value and until V_{DD} reaches 1.7 V (see *Figure 9*).
- Otherwise, if the time for V_{CAP_1} and V_{CAP_2} to reach V_{12} minimum value is slower than the time for V_{DD} to reach 1.7 V, then PA0 could be asserted low externally (see *Figure 10*).
- If V_{CAP_1} and V_{CAP_2} go below V_{12} minimum value and V_{DD} is higher than 1.7 V, then a reset must be asserted on PA0 pin.

Note: The minimum value of V_{12} depends on the maximum frequency targeted in the application (see Table 17: General operating conditions).

3.18.3 Regulator ON/OFF and internal reset ON/OFF availability

Table 4. Regulator ON/OFF and internal reset ON/OFF availability

Package	Regulator ON	Regulator OFF	Internal reset ON	Internal reset OFF
LQFP100	Yes	No	Yes	No
LQFP144, LQFP208			Yes PDR_ON set to V_{DD}	Yes PDR_ON connected to an external power supply supervisor
WLCSP143, LQFP176, UFBGA169, UFBGA176, TFBGA216	Yes BYPASS_REG set to V_{SS}	Yes BYPASS_REG set to V_{DD}		

3.19 Real-time clock (RTC), backup SRAM and backup registers

The backup domain includes:

- The real-time clock (RTC)
- 4 Kbytes of backup SRAM
- 20 backup registers

The real-time clock (RTC) is an independent BCD timer/counter. Dedicated registers contain the second, minute, hour (in 12/24 hour), week day, date, month, year, in BCD (binary-coded decimal) format. Correction for 28, 29 (leap year), 30, and 31 day of the month are performed automatically. The RTC provides a programmable alarm and programmable periodic interrupts with wakeup from Stop and Standby modes. The sub-seconds value is also available in binary format.

It is clocked by a 32.768 kHz external crystal, resonator or oscillator, the internal low-power RC oscillator or the high-speed external clock divided by 128. The internal low-speed RC has a typical frequency of 32 kHz. The RTC can be calibrated using an external 512 Hz output to compensate for any natural quartz deviation.

Two alarm registers are used to generate an alarm at a specific time and calendar fields can be independently masked for alarm comparison. To generate a periodic interrupt, a 16-bit programmable binary auto-reload downcounter with programmable resolution is available and allows automatic wakeup and periodic alarms from every 120 µs to every 36 hours.

A 20-bit prescaler is used for the time base clock. It is by default configured to generate a time base of 1 second from a clock at 32.768 kHz.

The 4-Kbyte backup SRAM is an EEPROM-like memory area. It can be used to store data which need to be retained in VBAT and standby mode. This memory area is disabled by default to minimize power consumption (see *Section 3.20: Low-power modes*). It can be enabled by software.

The backup registers are 32-bit registers used to store 80 bytes of user application data when V_{DD} power is not present. Backup registers are not reset by a system, a power reset, or when the device wakes up from the Standby mode (see *Section 3.20: Low-power modes*).

Table 9. Legend/abbreviations used in the pinout table

Name	Abbreviation	Definition
Pin name	Unless otherwise specified in brackets below the pin name, the pin function during and after reset is the same as the actual pin name	
Pin type	S	Supply pin
	I	Input only pin
	I/O	Input / output pin
I/O structure	FT	5 V tolerant I/O
	TTa	3.3 V tolerant I/O directly connected to ADC
	B	Dedicated BOOT0 pin
	RST	Bidirectional reset pin with weak pull-up resistor
Notes	Unless otherwise specified by a note, all I/Os are set as floating inputs during and after reset	
Alternate functions	Functions selected through GPIOx_AFR registers	
Additional functions	Functions directly selected/enabled through peripheral registers	

Table 10. STM32F427xx and STM32F429xx pin and ball definitions

Pin number								Pin name (function after reset)(1)	Pin type	I / O structure	Notes	Alternate functions	Additional functions
LQFP100	LQFP144	UFBGA169	UFBGA176	LQFP176	WLCSP143	LQFP208	TFBGA216						
1	1	B2	A2	1	D8	1	A3	PE2	I/O	FT	-	TRACECLK, SPI4_SCK, SAI1_MCLK_A, ETH_MII_TXD3, FMC_A23, EVENTOUT	-
2	2	C1	A1	2	C10	2	A2	PE3	I/O	FT	-	TRACED0, SAI1_SD_B, FMC_A19, EVENTOUT	-
3	3	C2	B1	3	B11	3	A1	PE4	I/O	FT	-	TRACED1, SPI4_NSS, SAI1_FS_A, FMC_A20, DCMI_D4, LCD_B0, EVENTOUT	-

Table 10. STM32F427xx and STM32F429xx pin and ball definitions (continued)

Pin number								Pin name (function after reset)[1]	Pin type	I / O structure	Notes	Alternate functions	Additional functions
LQFP100	LQFP144	UFBGA169	UFBGA176	LQFP176	WLCSP143	LQFP208	TFBGA216						
49	71	N9	M10	81	N2	92	L11	V_{CAP_1}	S	-	-	-	-
-	-	-	-	-	H2	93	K9	V_{SS}	S	-	-	-	-
50	72	F8	N10	82	J6	94	L10	V_{DD}	S	-	-	-	-
-	-	-	-	-	-	95	M14	PJ5	I/O	-	-	LCD_R6, EVENTOUT	-
-	-	N10	M11	83	-	96	P13	PH6	I/O	FT	-	I2C2_SMBA, SPI5_SCK, TIM12_CH1, ETH_MII_RXD2, FMC_SDNE1, DCMI_D8, EVENTOUT	-
-	-	M10	N12	84	-	97	N13	PH7	I/O	FT	-	I2C3_SCL, SPI5_MISO, ETH_MII_RXD3, FMC_SDCKE1, DCMI_D9, EVENTOUT	-
-	-	L10	M12	85	-	98	P14	PH8	I/O	FT	-	I2C3_SDA, FMC_D16, DCMI_HSYNC, LCD_R2, EVENTOUT	-
-	-	K10	M13	86	-	99	N14	PH9	I/O	FT	-	I2C3_SMBA, TIM12_CH2, FMC_D17, DCMI_D0, LCD_R3, EVENTOUT	-
-	-	N11	L13	87	-	100	P15	PH10	I/O	FT	-	TIM5_CH1, FMC_D18, DCMI_D1, LCD_R4, EVENTOUT	-
-	-	M11	L12	88	-	101	N15	PH11	I/O	FT	-	TIM5_CH2, FMC_D19, DCMI_D2, LCD_R5, EVENTOUT	-
-	-	L11	K12	89	-	102	M15	PH12	I/O	FT	-	TIM5_CH3, FMC_D20, DCMI_D3, LCD_R6, EVENTOUT	-
-	-	E7	H12	90	-	-	K10	V_{SS}	S	-	-	-	-
-	-	H8	J12	91	-	103	K11	V_{DD}	S	-	-	-	-

Table 12. STM32F427xx and STM32F429xx alternate function mapping (continued)

Port		AF0	AF1	AF2	AF3	AF4	AF5	AF6	AF7	AF8	AF9	AF10	AF11	AF12	AF13	AF14	AF15
		SYS	TIM1/2	TIM3/4/5	TIM8/9/10/11	I2C1/2/3	SPI1/2/3/4/5/6	SPI2/3/SAI1	SPI3/USART1/2/3	USART6/UART4/5/7/8	CAN1/2/TIM12/13/14/LCD	OTG2_HS/OTG1_FS	ETH	FMC/SDIO/OTG2_FS	DCMI	LCD	SYS
Port G	PG9	-	-	-	-	-	-	-	-	USART6_RX	-	-	-	FMC_NE2/FMC_NCE3	DCMI_VSYNC (1)	-	EVENTOUT
	PG10	-	-	-	-	-	-	-	-	-	LCD_G3	-	-	FMC_NCE4_1/FMC_NE3	DCMI_D2	LCD_B2	EVENTOUT
	PG11	-	-	-	-	-	-	-	-	-	-	-	ETH_MII_TX_EN/ETH_RMII_TX_EN	FMC_NCE4_2	DCMI_D3	LCD_B3	EVENTOUT
	PG12	-	-	-	-	-	SPI6_MISO	-	-	USART6_RTS	LCD_B4	-	-	FMC_NE4	-	LCD_B1	EVENTOUT
	PG13	-	-	-	-	-	SPI6_SCK	-	-	USART6_CTS	-	-	ETH_MII_TXD0/ETH_RMII_TXD0	FMC_A24	-	-	EVENTOUT
	PG14	-	-	-	-	-	SPI6_MOSI	-	-	USART6_TX	-	-	ETH_MII_TXD1/ETH_RMII_TXD1	FMC_A25	-	-	EVENTOUT
	PG15	-	-	-	-	-	-	-	-	USART6_CTS	-	-	-	FMC_SDNCAS	DCMI_D13	-	EVENTOUT
Port H	PH0	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	EVENTOUT
	PH1	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	EVENTOUT
	PH2	-	-	-	-	-	-	-	-	-	-	-	ETH_MII_CRS	FMC_SDCKE0	-	LCD_R0	EVENTOUT
	PH3	-	-	-	-	-	-	-	-	-	-	-	ETH_MII_COL	FMC_SDNE0	-	LCD_R1	EVENTOUT
	PH4	-	-	-	-	I2C2_SCL	-	-	-	-	-	OTG_HS_ULPI_NXT	-	-	-	-	EVENTOUT
	PH5	-	-	-	-	I2C2_SDA	SPI5_NSS	-	-	-	-	-	-	FMC_SDNWE	-	-	EVENTOUT
	PH6	-	-	-	-	I2C2_SMBA	SPI5_SCK	-	-	-	TIM12_CH1	-	-	FMC_SDNE1	DCMI_D8	-	-

6.3 Operating conditions

6.3.1 General operating conditions

Table 17. General operating conditions

Symbol	Parameter	Conditions[1]		Min	Typ	Max	Unit
f_{HCLK}	Internal AHB clock frequency	Power Scale 3 (VOS[1:0] bits in PWR_CR register = 0x01), Regulator ON, over-drive OFF		0	-	120	MHz
		Power Scale 2 (VOS[1:0] bits in PWR_CR register = 0x10), Regulator ON	Over-drive OFF	0	-	144	
			Over-drive ON		-	168	
		Power Scale 1 (VOS[1:0] bits in PWR_CR register= 0x11), Regulator ON	Over-drive OFF	0	-	168	
			Over-drive ON		-	180	
f_{PCLK1}	Internal APB1 clock frequency	Over-drive OFF		0	-	42	
		Over-drive ON		0	-	45	
f_{PCLK2}	Internal APB2 clock frequency	Over-drive OFF		0	-	84	
		Over-drive ON		0	-	90	
V_{DD}	Standard operating voltage			1.7[2]	-	3.6	V
V_{DDA} [3][4]	Analog operating voltage (ADC limited to 1.2 M samples)	Must be the same potential as V_{DD}[5]		1.7[2]	-	2.4	
	Analog operating voltage (ADC limited to 2.4 M samples)			2.4	-	3.6	
V_{BAT}	Backup operating voltage			1.65	-	3.6	
V_{12}	Regulator ON: 1.2 V internal voltage on V_{CAP_1}/V_{CAP_2} pins	Power Scale 3 ((VOS[1:0] bits in PWR_CR register = 0x01), 120 MHz HCLK max frequency		1.08	1.14	1.20	V
		Power Scale 2 ((VOS[1:0] bits in PWR_CR register = 0x10), 144 MHz HCLK max frequency with over-drive OFF or 168 MHz with over-drive ON		1.20	1.26	1.32	
		Power Scale 1 ((VOS[1:0] bits in PWR_CR register = 0x11), 168 MHz HCLK max frequency with over-drive OFF or 180 MHz with over-drive ON		1.26	1.32	1.40	
	Regulator OFF: 1.2 V external voltage must be supplied from external regulator on V_{CAP_1}/V_{CAP_2} pins[6]	Max frequency 120 MHz		1.10	1.14	1.20	
		Max frequency 144 MHz		1.20	1.26	1.32	
		Max frequency 168 MHz		1.26	1.32	1.38	

Table 27. Typical and maximum current consumptions in Stop mode

Symbol	Parameter	Conditions	Typ	Max(1)			Unit
				V_{DD} = 3.6 V			
			T_A = 25 °C	T_A = 25 °C	T_A = 85 °C	T_A = 105 °C	
$I_{DD\_STOP\_NM}$ (normal mode)	Supply current in Stop mode with voltage regulator in main regulator mode	Flash memory in Stop mode, all oscillators OFF, no independent watchdog	0.40	1.50	14.00	25.00	mA
		Flash memory in Deep power down mode, all oscillators OFF, no independent watchdog	0.35	1.50	14.00	25.00	
	Supply current in Stop mode with voltage regulator in Low Power regulator mode	Flash memory in Stop mode, all oscillators OFF, no independent watchdog	0.29	1.10	10.00	18.00	
		Flash memory in Deep power down mode, all oscillators OFF, no independent watchdog	0.23	1.10	10.00	18.00	
$I_{DD\_STOP\_UDM}$ (under-drive mode)	Supply current in Stop mode with voltage regulator in main regulator and under-drive mode	Flash memory in Deep power down mode, main regulator in under-drive mode, all oscillators OFF, no independent watchdog	0.19	0.50	6.00	9.00	
	Supply current in Stop mode with voltage regulator in Low Power regulator and under-drive mode	Flash memory in Deep power down mode, Low Power regulator in under-drive mode, all oscillators OFF, no independent watchdog	0.10	0.40	4.00	7.00	

1. Data based on characterization, tested in production.

Table 28. Typical and maximum current consumptions in Standby mode

Symbol	Parameter	Conditions	Typ(1)			Max(2)			Unit
			T_A = 25 °C			T_A = 25 °C	T_A = 85 °C	T_A = 105 °C	
			V_{DD} = 1.7 V	V_{DD}= 2.4 V	V_{DD} = 3.3 V	V_{DD} = 3.6 V			
I_{DD_STBY}	Supply current in Standby mode	Backup SRAM ON, low-speed oscillator (LSE) and RTC ON	2.80	3.00	3.60	7.00	19.00	36.00	µA
		Backup SRAM OFF, low-speed oscillator (LSE) and RTC ON	2.30	2.60	3.10	6.00	16.00	31.00	
		Backup SRAM ON, RTC and LSE OFF	2.30	2.50	2.90	6.00(3)	18.00(3)	35.00(3)	
		Backup SRAM OFF, RTC and LSE OFF	1.70	1.90	2.20	5.00(3)	15.00(3)	30.00(3)	

1. The typical current consumption values are given with PDR OFF (internal reset OFF). When the PDR is OFF (internal reset OFF), the typical current consumption is reduced by additional 1.2 µA.
2. Based on characterization, not tested in production unless otherwise specified.
3. Based on characterization, tested in production.

Table 29. Typical and maximum current consumptions in V_{BAT} mode

Symbol	Parameter	Conditions(1)	Typ			Max(2)		Unit
			T_A = 25 °C			T_A = 85 °C	T_A = 105 °C	
			V_{BAT} = 1.7 V	V_{BAT}= 2.4 V	V_{BAT} = 3.3 V	V_{BAT} = 3.6 V		
I_{DD_VBAT}	Backup domain supply current	Backup SRAM ON, low-speed oscillator (LSE) and RTC ON	1.28	1.40	1.62	6	11	µA
		Backup SRAM OFF, low-speed oscillator (LSE) and RTC ON	0.66	0.76	0.97	3	5	
		Backup SRAM ON, RTC and LSE OFF	0.70	0.72	0.74	5	10	
		Backup SRAM OFF, RTC and LSE OFF	0.10	0.10	0.10	2	4	

1. Crystal used: Abracon ABS07-120-32.768 kHz-T with a C_L of 6 pF for typical values.
2. Guaranteed by characterization results.

Table 31. Typical current consumption in Run mode, code with data processing running from Flash memory, regulator OFF (ART accelerator enabled except prefetch)(1)

Symbol	Parameter	Conditions	f_{HCLK} (MHz)	VDD=3.3 V		VDD=1.7 V		Unit
				I_{DD12}	I_{DD}	I_{DD12}	I_{DD}	
I_{DD12} / I_{DD}	Supply current in RUN mode from V_{12} and V_{DD} supply	All Peripherals enabled	168	77.8	1.3	76.8	1.0	mA
			150	70.8	1.3	69.8	1.0	
			144	64.5	1.3	63.6	1.0	
			120	49.9	1.2	49.3	0.9	
			90	39.2	1.3	38.7	1.0	
			60	27.2	1.2	26.8	0.9	
			30	15.6	1.2	15.4	0.9	
			25	13.6	1.2	13.5	0.9	
		All Peripherals disabled	168	38.2	1.3	37.0	1.0	
			150	34.6	1.3	33.4	1.0	
			144	31.3	1.3	30.3	1.0	
			120	24.0	1.2	23.2	0.9	
			90	18.1	1.4	18.0	1.0	
			60	12.9	1.2	12.5	0.9	
			30	7.2	1.2	6.9	0.9	
			25	6.3	1.2	6.1	0.9	

1. When peripherals are enabled, the power consumption corresponding to the analog part of the peripherals (such as ADC, or DAC) is not included.

On-chip peripheral current consumption

The MCU is placed under the following conditions:

- At startup, all I/O pins are in analog input configuration.
- All peripherals are disabled unless otherwise mentioned.
- I/O compensation cell enabled.
- The ART accelerator is ON.
- Scale 1 mode selected, internal digital voltage V12 = 1.32 V.
- HCLK is the system clock. $f_{PCLK1} = f_{HCLK}/4$, and $f_{PCLK2} = f_{HCLK}/2$.
  The given value is calculated by measuring the difference of current consumption
  - with all peripherals clocked off
  - with only one peripheral clocked on
  - f_{HCLK} = 180 MHz (Scale1 + over-drive ON), f_{HCLK} = 144 MHz (Scale 2), f_{HCLK} = 120 MHz (Scale 3)"
- Ambient operating temperature is 25 °C and V_{DD}=3.3 V.

Table 35. Peripheral current consumption

Peripheral		I_{DD}(Typ)(1)			Unit
		Scale 1	Scale 2	Scale 3	
AHB1 (up to 180 MHz)	GPIOA	2.50	2.36	2.08	µA/MHz
	GPIOB	2.56	2.36	2.08	
	GPIOC	2.44	2.29	2.00	
	GPIOD	2.50	2.36	2.08	
	GPIOE	2.44	2.29	2.00	
	GPIOF	2.44	2.29	2.00	
	GPIOG	2.39	2.22	2.00	
	GPIOH	2.33	2.15	1.92	
	GPIOI	2.39	2.22	2.00	
	GPIOJ	2.33	2.15	1.92	
	GPIOK	2.33	2.15	1.92	
	OTG_HS+ULPI	27.00	24.86	21.92	
	CRC	0.44	0.42	0.33	
	BKPSRAM	0.78	0.69	0.58	
	DMA1	25.33	23.26	20.50	
	DMA2	24.72	22.71	20.00	
	DMA2D	28.50	26.32	23.33	
	ETH_MAC ETH_MAC_TX ETH_MAC_RX ETH_MAC_PTP	21.56	20.07	17.75	

Table 69. USB HS clock timing parameters(1)

Symbol	Parameter		Min	Typ	Max	Unit
	f_{HCLK} value to guarantee proper operation of USB HS interface		30	-	-	MHz
F_{START_8BIT}	Frequency (first transition)	8-bit ±10%	54	60	66	MHz
F_{STEADY}	Frequency (steady state) ±500 ppm		59.97	60	60.03	MHz
D_{START_8BIT}	Duty cycle (first transition)	8-bit ±10%	40	50	60	%
D_{STEADY}	Duty cycle (steady state) ±500 ppm		49.975	50	50.025	%
t_{STEADY}	Time to reach the steady state frequency and duty cycle after the first transition		-	-	1.4	ms
t_{START_DEV}	Clock startup time after the de-assertion of SuspendM	Peripheral	-	-	5.6	ms
t_{START_HOST}		Host	-	-	-	
t_{PREP}	PHY preparation time after the first transition of the input clock		-	-	-	µs

1. Guaranteed by design.

Figure 46. ULPI timing diagram

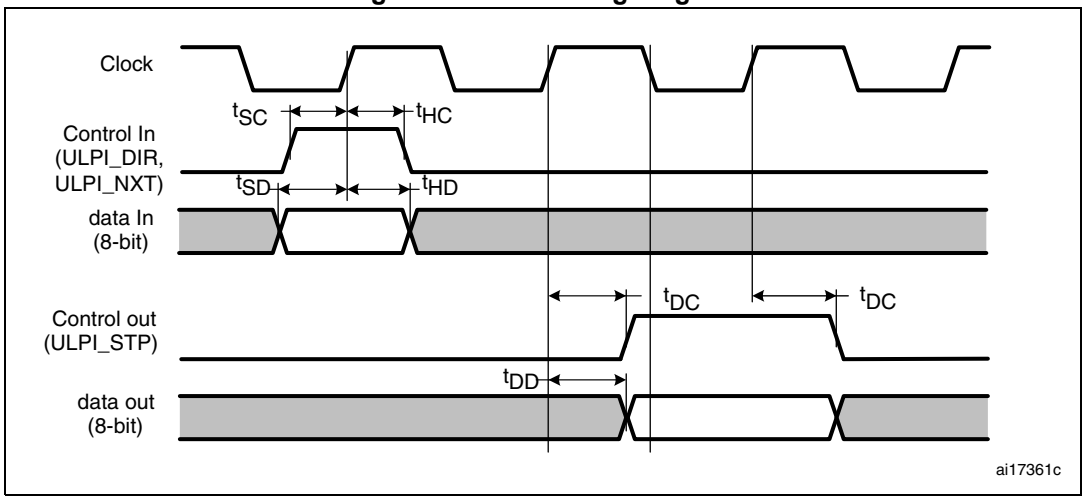
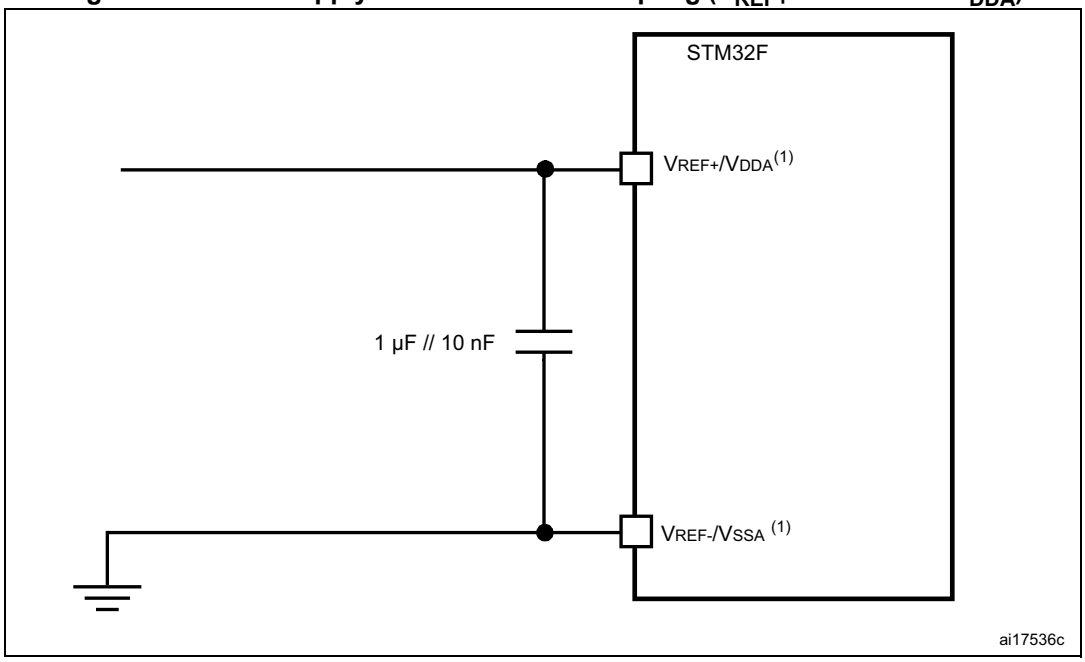


Figure 53. Power supply and reference decoupling (V_{REF+} connected to V_{DDA})



1. V_{REF+} and V_{REF-} inputs are both available on UFBGA176. V_{REF+} is also available on LQFP100, LQFP144, and LQFP176. When V_{REF+} and V_{REF-} are not available, they are internally connected to V_{DDA} and V_{SSA}.

6.3.22 Temperature sensor characteristics

Table 80. Temperature sensor characteristics

Symbol	Parameter	Min	Typ	Max	Unit
T_L(1)	V_{SENSE} linearity with temperature	-	±1	±2	°C
Avg_Slope(1)	Average slope	-	2.5		mV/°C
V_{25}(1)	Voltage at 25 °C	-	0.76		V
t_{START}(2)	Startup time	-	6	10	µs
T_{S_temp}(2)	ADC sampling time when reading the temperature (1 °C accuracy)	10	-	-	µs

1. Guaranteed by characterization results.
2. Guaranteed by design.

Table 81. Temperature sensor calibration values

Symbol	Parameter	Memory address
TS_CAL1	TS ADC raw data acquired at temperature of 30 °C, V_{DDA}= 3.3 V	0x1FFF 7A2C - 0x1FFF 7A2D
TS_CAL2	TS ADC raw data acquired at temperature of 110 °C, V_{DDA}= 3.3 V	0x1FFF 7A2E - 0x1FFF 7A2F

6.3.23 V_{BAT} monitoring characteristics

Table 82. V_{BAT} monitoring characteristics

Symbol	Parameter	Min	Typ	Max	Unit
R	Resistor bridge for V_{BAT}	-	50	-	KΩ
Q	Ratio on V_{BAT} measurement	-	4	-	
Er(1)	Error on Q	–1	-	+1	%
T_{S_vbat}(2)(2)	ADC sampling time when reading the V_{BAT} 1 mV accuracy	5	-	-	µs

1. Guaranteed by design.
2. Shortest sampling time can be determined in the application by multiple iterations.

6.3.24 Reference voltage

The parameters given in *Table 83* are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in *Table 17*.

Table 83. internal reference voltage

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{REFINT}	Internal reference voltage	–40 °C < T_A < +105 °C	1.18	1.21	1.24	V
$T_{S\_vrefint}$(1)	ADC sampling time when reading the internal reference voltage		10	-	-	µs
V_{RERINT_s}(2)	Internal reference voltage spread over the temperature range	V_{DD} = 3V ± 10mV	-	3	5	mV
T_{Coeff}(2)	Temperature coefficient		-	30	50	ppm/°C
t_{START}(2)	Startup time		-	6	10	µs

1. Shortest sampling time can be determined in the application by multiple iterations.
2. Guaranteed by design, not tested in production

Table 84. Internal reference voltage calibration values

Symbol	Parameter	Memory address
V_{REFIN_CAL}	Raw data acquired at temperature of 30 °C $_{VDDA}$ = 3.3 V	0x1FFF 7A2A - 0x1FFF 7A2B

6.3.25 DAC electrical characteristics

Table 85. DAC characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit	Comments
V_{DDA}	Analog supply voltage	-		$1.7^{(1)}$	-	3.6	V	-
V_{REF+}	Reference supply voltage	-		$1.7^{(1)}$	-	3.6	V	$V_{REF+} \leq V_{DDA}$
V_{SSA}	Ground	-		0	-	0	V	-
$R_{LOAD}^{(2)}$	Resistive load	DAC output buffer ON	R_{LOAD} connected to V_{SSA}	5	-	-	kΩ	-
			R_{LOAD} connected to V_{DDA}	25				-
$R_O^{(2)}$	Impedance output with buffer OFF	-		-	-	15	kΩ	When the buffer is OFF, the Minimum resistive load between DAC_OUT and V_{SS} to have a 1% accuracy is 1.5 MΩ
$C_{LOAD}^{(2)}$	Capacitive load	-		-	-	50	pF	Maximum capacitive load at DAC_OUT pin (when the buffer is ON).
DAC_OUT $min^{(2)}$	Lower DAC_OUT voltage with buffer ON	-		0.2	-	-	V	It gives the maximum output excursion of the DAC. It corresponds to 12-bit input code (0x0E0) to (0xF1C) at V_{REF+} = 3.6 V and (0x1C7) to (0xE38) at V_{REF+} = 1.7 V
DAC_OUT $max^{(2)}$	Higher DAC_OUT voltage with buffer ON	-		-	-	V_{DDA} – 0.2	V	
DAC_OUT $min^{(2)}$	Lower DAC_OUT voltage with buffer OFF	-		-	0.5	-	mV	It gives the maximum output excursion of the DAC.
DAC_OUT $max^{(2)}$	Higher DAC_OUT voltage with buffer OFF	-		-	-	V_{REF+} – 1LSB	V	
$I_{VREF+}^{(4)}$	DAC DC V_{REF} current consumption in quiescent mode (Standby mode)	-		-	170	240	µA	With no load, worst code (0x800) at V_{REF+} = 3.6 V in terms of DC consumption on the inputs
		-		-	50	75		With no load, worst code (0xF1C) at V_{REF+} = 3.6 V in terms of DC consumption on the inputs

Figure 58. Asynchronous multiplexed PSRAM/NOR write waveforms

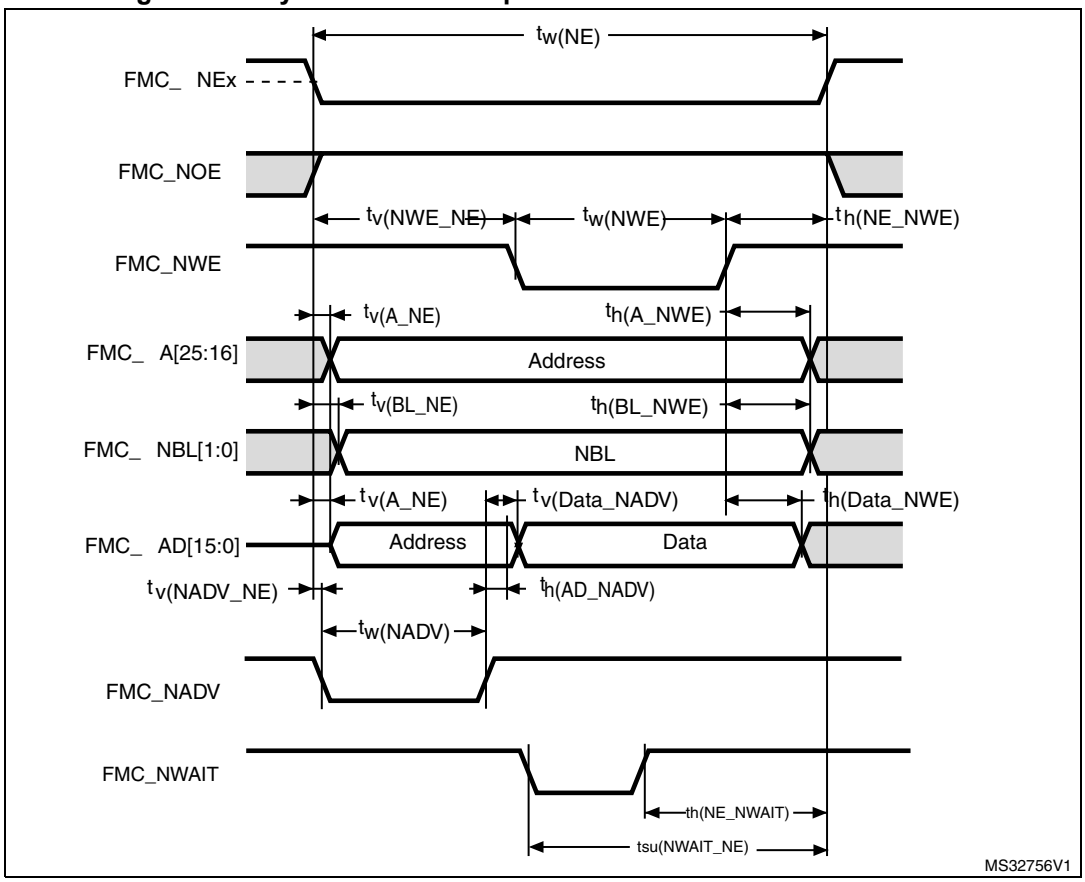


Table 92. Asynchronous multiplexed PSRAM/NOR write timings(1)(2)

Symbol	Parameter	Min	Max	Unit
$t_{w(NE)}$	FMC_NE low time	$4T_{HCLK}$	$4T_{HCLK}+0.5$	ns
$t_{v(NWE\_NE)}$	FMC_NEx low to FMC_NWE low	$T_{HCLK} - 1$	$T_{HCLK}+0.5$	ns
$t_{w(NWE)}$	FMC_NWE low time	$2T_{HCLK}$	$2T_{HCLK}+0.5$	ns
$t_{h(NE\_NWE)}$	FMC_NWE high to FMC_NE high hold time	T_{HCLK}	-	ns
$t_{v(A\_NE)}$	FMC_NEx low to FMC_A valid	-	0	ns
$t_{v(NADV\_NE)}$	FMC_NEx low to FMC_NADV low	0.5	1	ns
$t_{w(NADV)}$	FMC_NADV low time	$T_{HCLK} - 0.5$	$T_{HCLK}+ 0.5$	ns
$t_{h(AD\_NADV)}$	FMC_AD(adress) valid hold time after FMC_NADV high)	$T_{HCLK} - 2$	-	ns
$t_{h(A\_NWE)}$	Address hold time after FMC_NWE high	T_{HCLK}	-	ns
$t_{h(BL\_NWE)}$	FMC_BL hold time after FMC_NWE high	$T_{HCLK} - 2$	-	ns
$t_{v(BL\_NE)}$	FMC_NEx low to FMC_BL valid	-	2	ns
$t_{v(Data\_NADV)}$	FMC_NADV high to Data valid	-	$T_{HCLK}+1.5$	ns
$t_{h(Data\_NWE)}$	Data hold time after FMC_NWE high	$T_{HCLK}+0.5$	-	ns

1. C_L = 30 pF.
2. Guaranteed by characterization results.

Table 108. Dynamic characteristics: SD / MMC characteristics(1)(2)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{PP}	Clock frequency in data transfer mode		0		48	MHz
-	SDIO_CK/fPCLK2 frequency ratio		-	-	8/3	-
$t_{W(CKL)}$	Clock low time	fpp =48 MHz	8.5	9	-	ns
$t_{W(CKH)}$	Clock high time	fpp =48 MHz	8.3	10	-	
CMD, D inputs (referenced to CK) in MMC and SD HS mode						
t_{ISU}	Input setup time HS	fpp =48 MHz	3.5	-	-	ns
t_{IH}	Input hold time HS	fpp =48 MHz	0	-	-	
CMD, D outputs (referenced to CK) in MMC and SD HS mode						
t_{OV}	Output valid time HS	fpp =48 MHz	-	4.5	7	ns
t_{OH}	Output hold time HS	fpp =48 MHz	3	-	-	
CMD, D inputs (referenced to CK) in SD default mode						
tISUD	Input setup time SD	fpp =24 MHz	1.5	-	-	ns
tIHD	Input hold time SD	fpp =24 MHz	0.5	-	-	
CMD, D outputs (referenced to CK) in SD default mode						
tOVD	Output valid default time SD	fpp =24 MHz	-	4.5	6.5	ns
tOHD	Output hold default time SD	fpp =24 MHz	3.5	-	-	

1. Guaranteed by characterization results.
2. V_{DD} = 2.7 to 3.6 V.

6.3.30 RTC characteristics

Table 109. RTC characteristics

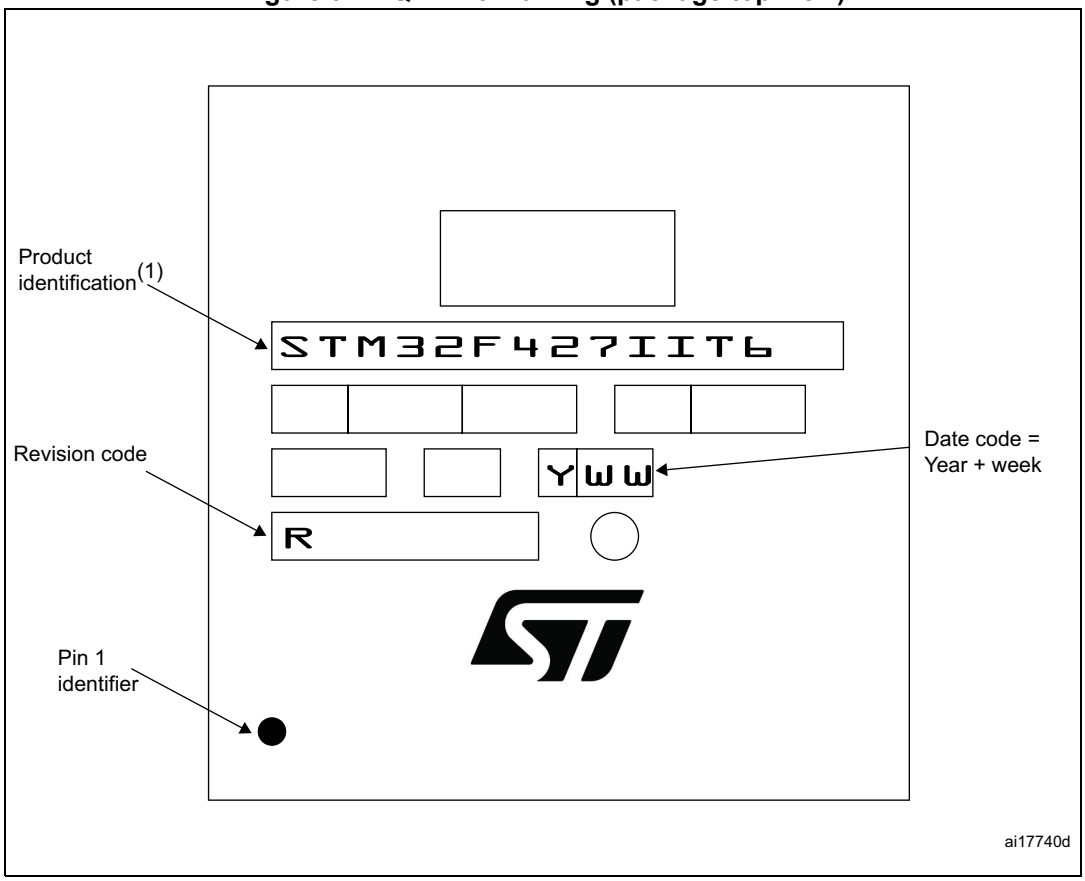
Symbol	Parameter	Conditions	Min	Max
-	f_{PCLK1}/RTCCLK frequency ratio	Any read/write operation from/to an RTC register	4	-

Device marking for LQFP176

The following figure gives an example of topside marking orientation versus pin 1 identifier location.

Other optional marking or inset/upset marks, which depends assembly location, are not indicated below.

Figure 91. LQFP176 marking (package top view)



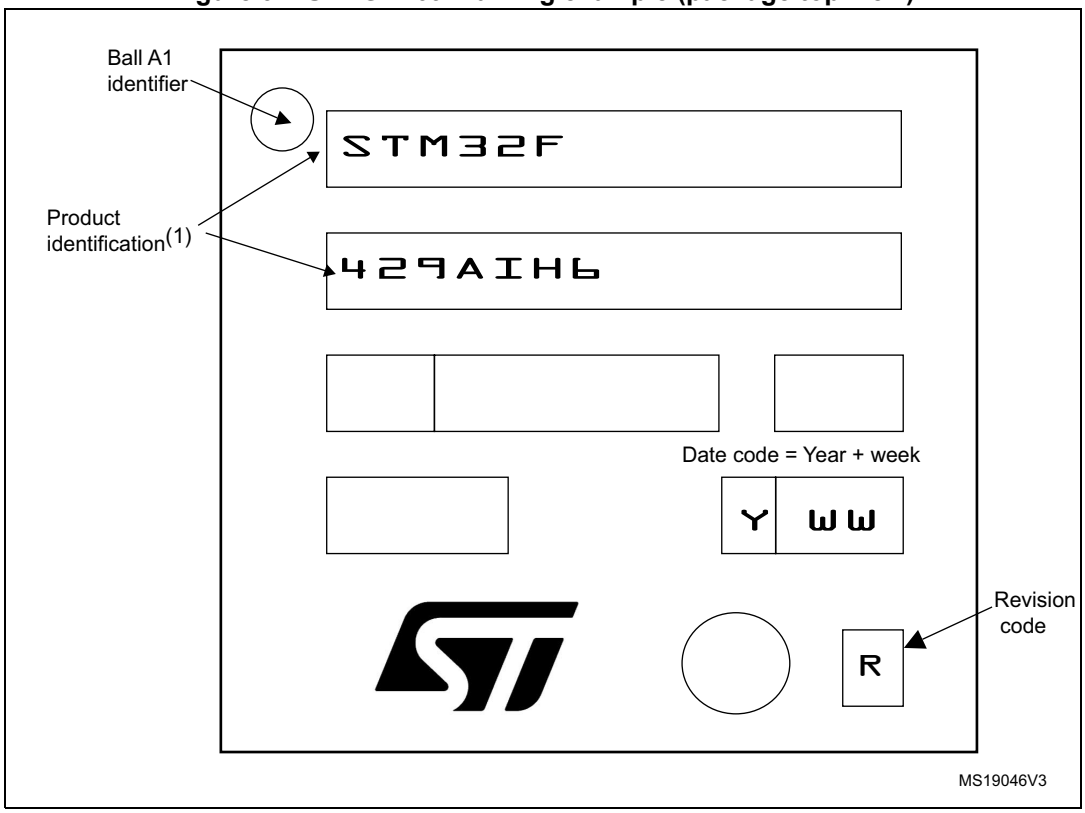
1. Parts marked as “ES”, “E” or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering Samples to run qualification activity.

Device marking for UFBGA169

The following figure gives an example of topside marking orientation versus ball A1 identifier location.

Other optional marking or inset/upset marks, which depends assembly location, are not indicated below.

Figure 97. UFBGA169 marking example (package top view)



1. Parts marked as “ES”, “E” or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering Samples to run qualification activity.

Table 124. Document revision history

Date	Revision	Changes
21-Jan-2016	8	Updated *Figure 22: Power supply scheme*. Added $t_{d(TXD)}$ values corresponding to 1.71 V < V_{DD} < 3.6 V in *Table 72: Dynamics characteristics: Ethernet MAC signals for RMII*.
18-Jul-2016	9	Updated *Figure 1: Compatible board design STM32F10xx/STM32F2xx/STM32F4xx for LQFP100 package*. Added mission profile compliance with JEDEC JESD47 in *Section 6.2: Absolute maximum ratings*. Changed *Figure 31 HSI deviation versus temperature to ACCHSI versus temperature.* Updated R_{LOAD} in *Table 85: DAC characteristics*. Added note *2.* related to the position of the 0.1 µF capacitor below *Figure 37: Recommended NRST pin protection*. Updated *Figure 40: SPI timing diagram - master mode*. Added reference to optional marking or inset/upset marks in all package device marking sections. Updated *Figure 85: WLCSP143 marking example (package top view)*, *Figure 88: LQFP144 marking example (package top view)*, *Figure 91: LQFP176 marking (package top view)*, *Figure 94: LQFP208 marking example (package top view)*. Updated *Figure 98: UFBGA176+25 - ball 10 x 10 mm, 0.65 mm pitch ultra thin fine pitch ball grid array package outline* and *Table 118: UFBGA176+25 - ball, 10 x 10 mm, 0.65 mm pitch, ultra fine pitch ball grid array package mechanical data*.